**Product data sheet** 

## 1. General description

Ultrafast, epitaxial rectifier diode in a SOD113 (TO-220F) plastic package.

### 2. Features and benefits

- Fast switching
- Low thermal resistance
- Soft recovery characteristic
- Isolated package
- Low forward voltage drop
- · High thermal cycling performance

### 3. Applications

- Output rectifiers in high frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			6	000		V
$I_{F(AV)}$	average forward current	$\delta$ = 0.5 ; square-wave pulse; $T_h \le 85$ °C; Fig. 1; Fig. 2; Fig. 3			9		А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_h \le$ 85 °C; square-wave pulse	18		А		
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	91			А	
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			Α		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	1.12	1.26	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C		-	1.03	-	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	0.97	1.11	V
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	32	60	ns

## 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A 001aaa020
2	А	anode		001aaa020
mb	mb	mounting base; isolated	1 2 SOD113 (2-lead TO-220F)	

## 6. Ordering information

**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
BYV29X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'	SOD113		

### 7. Marking

#### Table 4. Marking codes

Type number	Marking codes
BYV29X-600	BYV29X-600

## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		600	V
$V_{RWM}$	crest working reverse voltage		600	V
$V_R$	reverse voltage	DC	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; square-wave pulse; $T_h \le 85$ °C; Fig. 1; Fig. 2; Fig. 3	9	А
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_h \le 85 °C$ ; square-wave pulse	18	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	91	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	100	Α
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		150	°C

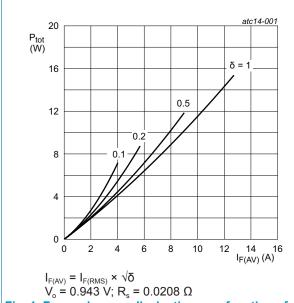
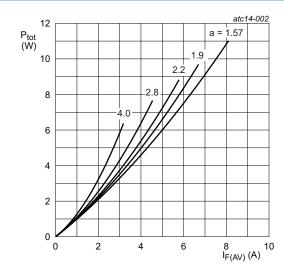


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$ Vo = 0.943 V; Rs = 0.0208  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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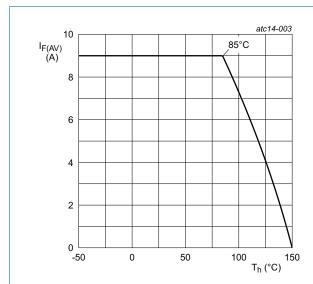


Fig. 3. Forward current as a function of heatsink temperature; maximum values

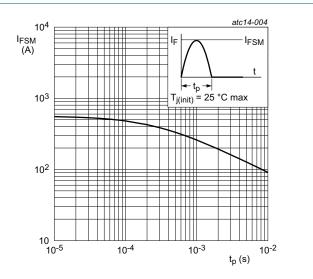
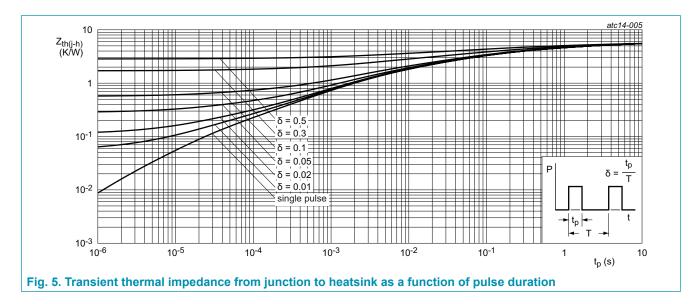


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance	with heatsink compound; Fig. 5	-	-	5.5	K/W
	from junction to heatsink	without heatsink compound	-	-	5.9	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



### 10. Isolation characteristics

**Table 6. Isolation characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from cathode to external heatsink	-	10	-	PF

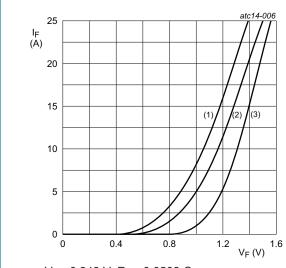
### 11. Characteristics

### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					•
V <sub>F</sub>	forward current	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.12	1.26	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C	-	1.03	-	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	0.97	1.11	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	2	50	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 100 °C	-	0.3	-	mA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 125 °C	-	-	3	mA
Dynamic	characteristics					
Q <sub>r</sub>	reverse charge		-	37	-	nC
t <sub>rr</sub>	reverse recovery time		-	32	60	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	2.3	-	Α
dI <sub>rr</sub> /dt	peak rate of fall of reverse recovery current		-	297	-	A/µs
Q <sub>r</sub>	reverse charge		-	220	-	nC
t <sub>rr</sub>	reverse recovery time		-	43	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	10	-	А
dI <sub>rr</sub> /dt	peak rate of fall of reverse recovery current		-	655	-	A/µs
$Q_r$	reverse charge		-	165	-	nC
t <sub>rr</sub>	reverse recovery time		-	59	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	5.6	-	А
dl <sub>rr</sub> /dt	peak rate of fall of reverse recovery current		-	215	-	A/µs
Q <sub>r</sub>	reverse charge		-	425	-	nC
t <sub>rr</sub>	reverse recovery time		-	57	-	ns
I <sub>RM</sub>	peak reverse recovery current	I <sub>F</sub> = 8 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	15	-	А
dl <sub>rr</sub> /dt	peak rate of fall of reverse recovery current		-	1661	-	A/µs
Q <sub>r</sub>	reverse charge		-	315	-	nC
t <sub>rr</sub>	reverse recovery time		-	70	-	ns
I <sub>RM</sub>	peak reverse recovery current	I <sub>F</sub> = 8 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	9	-	A
dI <sub>rr</sub> /dt	peak rate of fall of reverse recovery current		-	1181	-	A/µs

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 $V_o$  = 0.943 V;  $R_s$  = 0.0208  $\Omega$ 

 $V_0 = 0.343 \text{ V}, N_s = 0.0200 \Omega$ (1)  $T_j = 150 \text{ °C}$ ; typical values (2)  $T_j = 150 \text{ °C}$ ; maximum values (3)  $T_j = 25 \text{ °C}$ ; maximum values Fig. 6. Forward current as a function of forward voltage

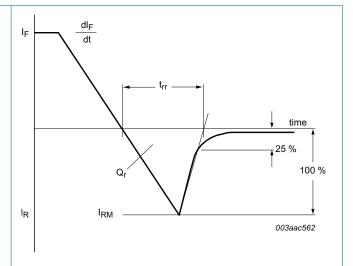
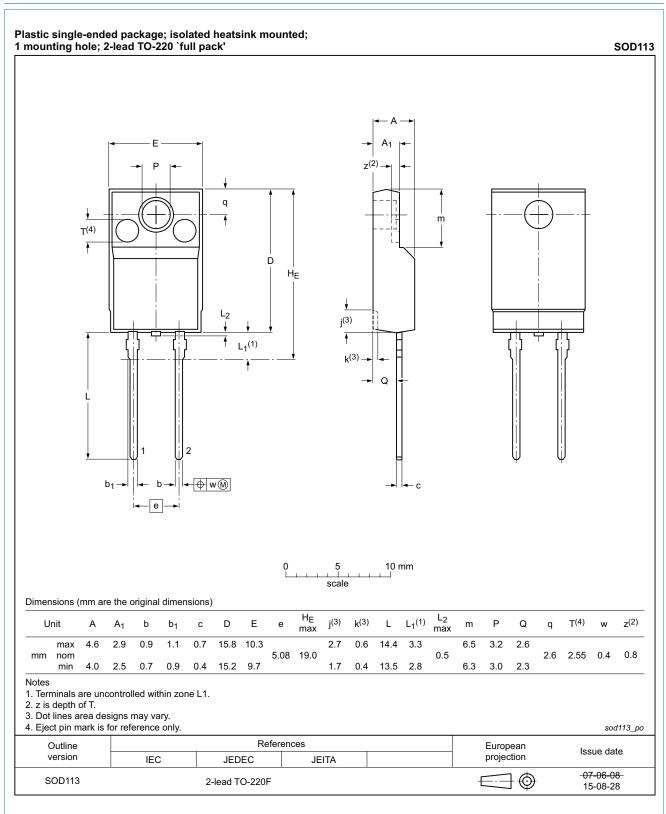


Fig. 7. Reverse recovery definitions; ramp recovery

## 12. Package outline



### 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BYV29X-600

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